



Description

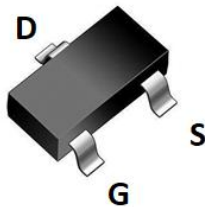
JMT P-channel Enhancement Mode Power MOSFET

Features

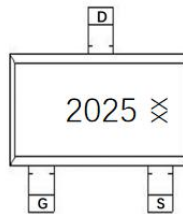
- -20V, -5A
 $R_{DS(ON)} < 26m\Omega @ V_{GS} = -4.5V$
 $R_{DS(ON)} < 37m\Omega @ V_{GS} = -2.5V$
- Advanced Trench Technology
- Provide Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

Application

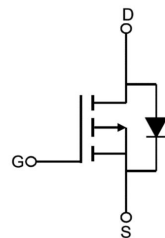
- Load Switch
- PWM Application
- Power management



SOT-23-3L top view



Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
2025	JMTJ250P02A	TAPING	SOT-23-3L	7inch	3000	120000

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	-20	V
V_{GSS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current	$T_A = 25^\circ C$	-5
		$T_A = 100^\circ C$	-3.25
I_{DM}	Pulsed Drain Current ^{note1}	-20	A
P_D	Power Dissipation	$T_A = 25^\circ C$	1.1
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	114	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$



Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -20V, V _{GS} =0V,	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±12V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = -250μA	-0.4	-0.7	-1.0	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note2</small>	V _{GS} = -4.5V, I _D = -5A	-	20	26	mΩ
		V _{GS} = -2.5V, I _D = -4A	-	27	37	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -10V, V _{GS} =0V, f=1.0MHz	-	1200	-	pF
C _{oss}	Output Capacitance		-	191	-	pF
C _{rss}	Reverse Transfer Capacitance		-	168	-	pF
Q _g	Total Gate Charge	V _{DS} = -10V, I _D = -5A, V _{GS} = -4.5V	-	33.7	-	nC
Q _{gs}	Gate-Source Charge		-	3.5	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	10.5	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -10V, I _D = -5A, V _{GS} = -4.5V, R _{GEN} =10Ω	-	11	-	ns
t _r	Turn-on Rise Time		-	35	-	ns
t _{d(off)}	Turn-off Delay Time		-	30	-	ns
t _f	Turn-off Fall Time		-	10	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-5	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-20	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = -5A	-	-	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%



Typical Performance Characteristics

Figure 1: Output Characteristics

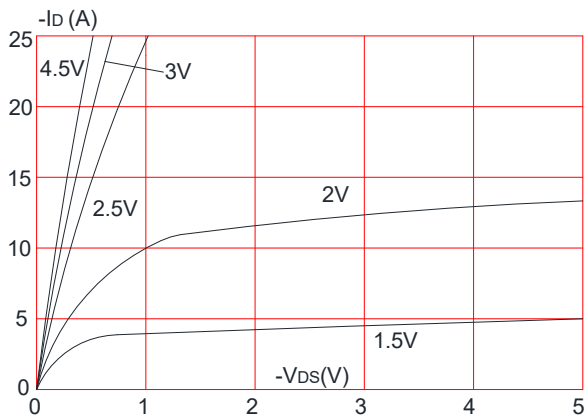


Figure 2: Typical Transfer Characteristics

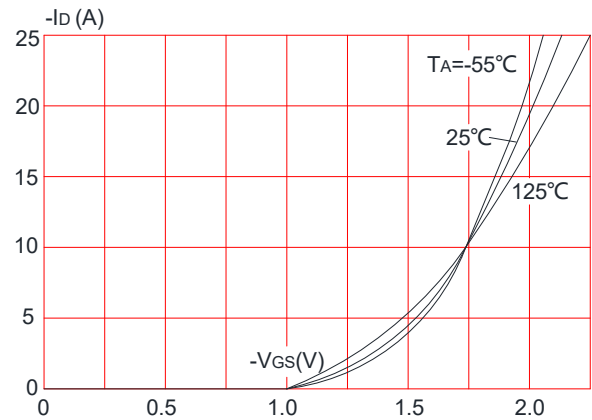


Figure 3: On-resistance vs. Drain Current

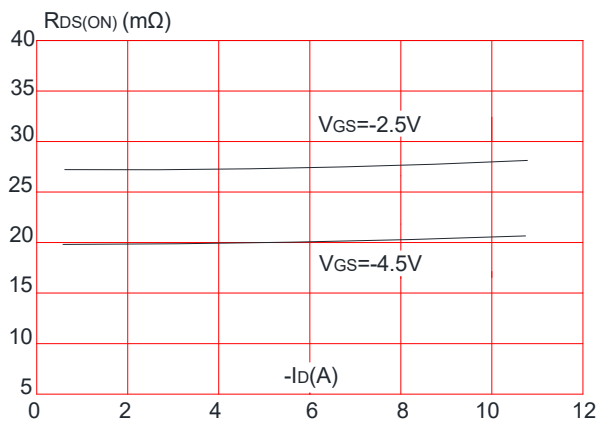


Figure 4: Body Diode Characteristics

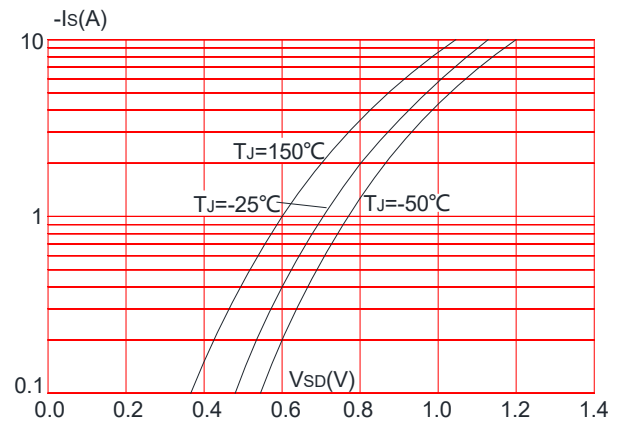


Figure 5: Gate Charge Characteristics

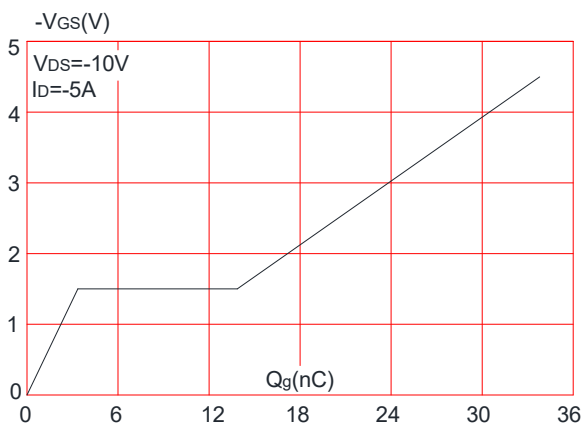


Figure 6: Capacitance Characteristics

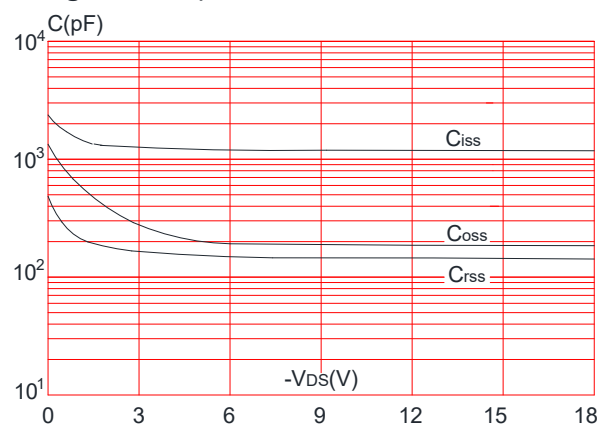




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

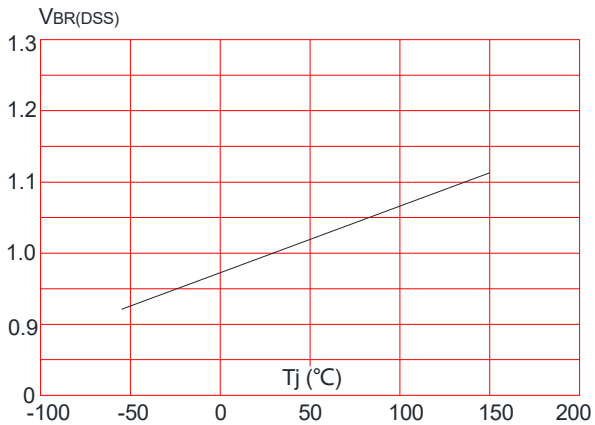


Figure 8: Normalized on Resistance vs. Junction Temperature

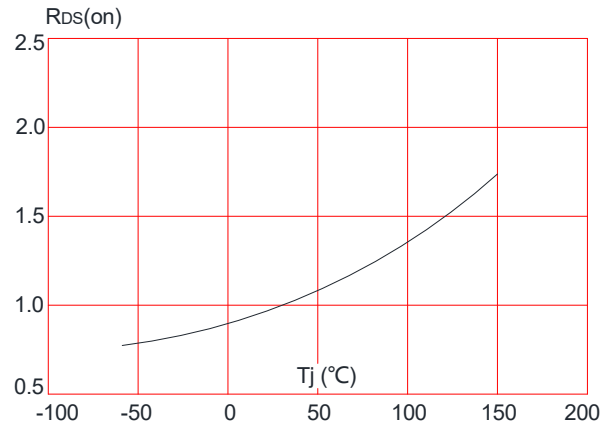


Figure 9: Maximum Safe Operating Area

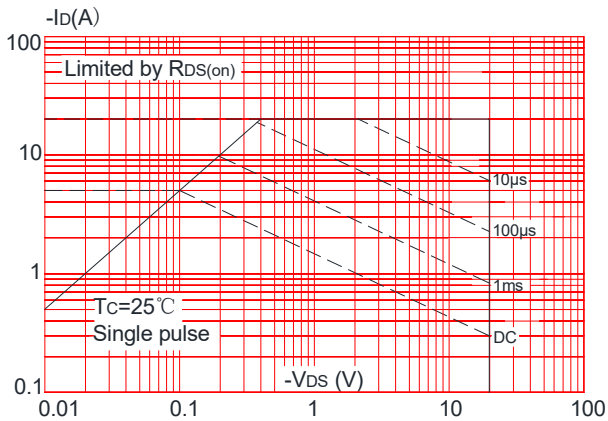


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

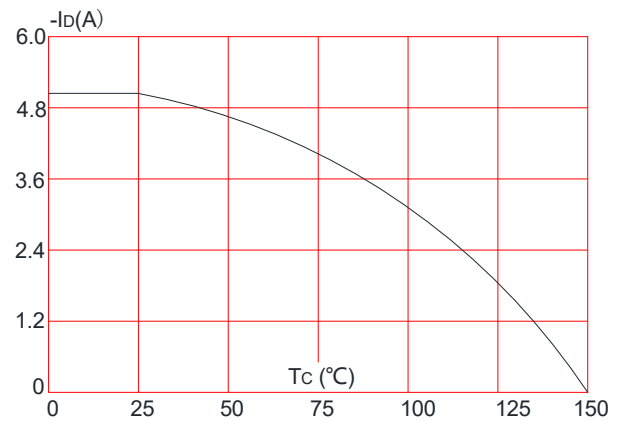
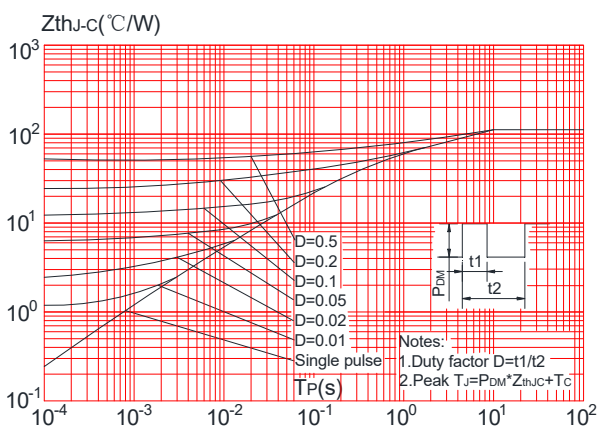
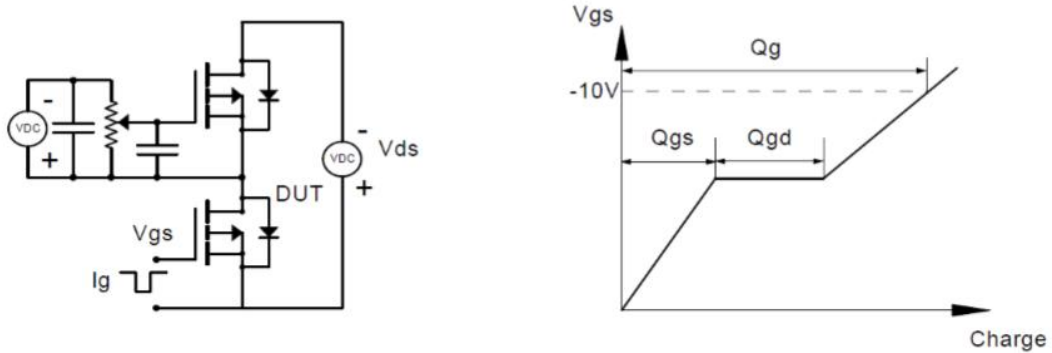


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

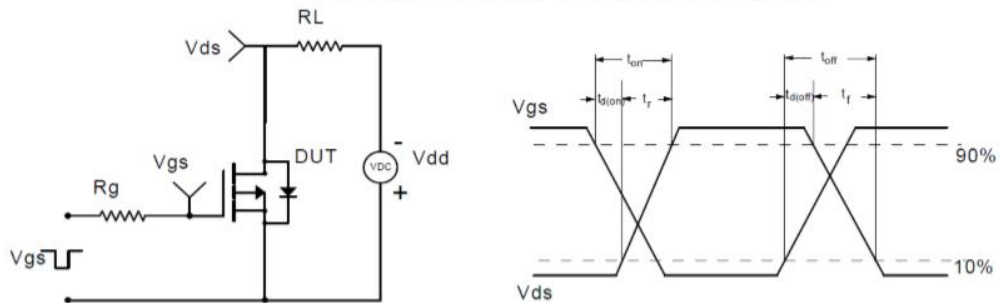


Test Circuit

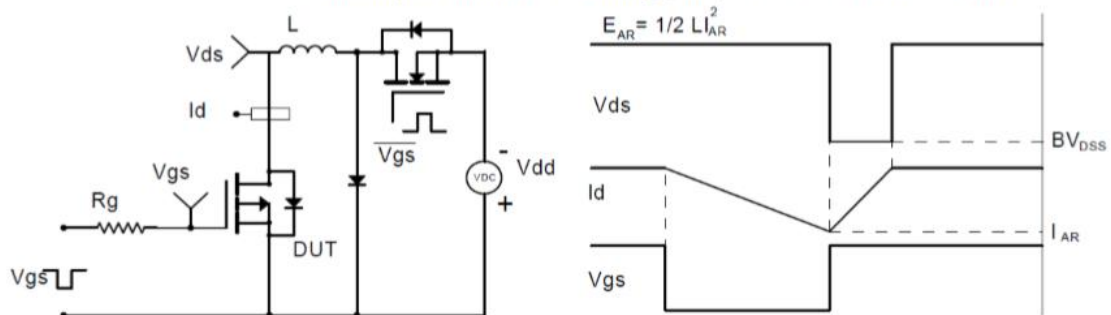
Gate Charge Test Circuit & Waveform



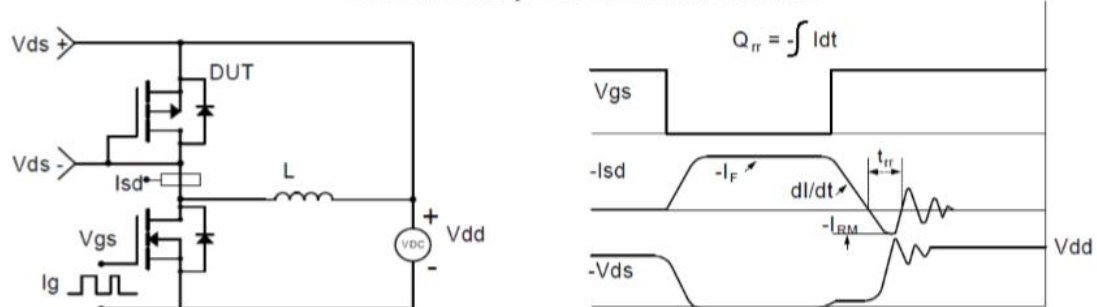
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

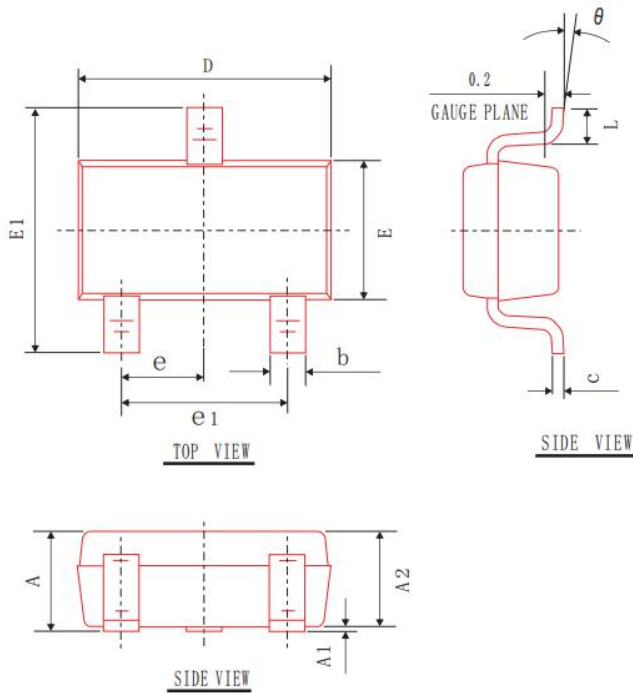


Diode Recovery Test Circuit & Waveforms





Package Mechanical Data-SOT-23-3L



COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	---	---	1.30
A1	0.00	0.05	0.10
A2	1.00	1.10	1.20
b	0.30	0.40	0.50
c	0.119	0.127	0.135
e1	1.80	1.90	2.00
D	2.80	2.90	3.00
E	1.50	1.60	1.70
E1	2.60	2.80	3.00
L	0.30	0.45	0.60
θ	0°	4°	8°
e	0.95BSC		

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